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Isolation of Open Defects Using Space Domain Reflectometry";  
"Localization of Dead Open in a Solder Bump by Space Domain Reflectometry"  
"Advanced Fault Isolation Technique Using Electro-Optical Terahertz Pulse Reflectometry (EOTPR) for 2D and 2.5D Flip-Chip Package"  
"Novel Plasma FIB/SEM for High Speed Failure Analysis and Real Time Imaging of Large Volume Removal"; "FemtoFarad/TeraOhm Endpoint Detection for Microsurgery of Integrated Circuit Devices"; "Fault Isolation and Failure Analysis of TSV"; "Cross Section Analysis of Cu Filled TSVs Based On High Throughput Plasma- FIB Milling";  
"Microstructural Considerations on the Reliability of 3D Packaging"  
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"Enhanced Comparison of Lock-in Thermography and Magnetic Microscopy for 3D Defect Localization of System in Packages"  
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"Study of Static Noise Margin, Cell Stability and Influence of Electron Beam on Sub-30 nm SRAM Using SEM-Based Nanoprobing with 8 Nanoprobes"  
"Leaky Device Channel Anomaly Identification and Case Study by Nano-Probing Technique, Curve Fitting, and Model Analysis";  
"Photon Based Techniques: An Understanding"; "Photon Emission Spectra of FETs as Obtained by InGaAs Detector"; "Near-Infrared Photon Emission Spectroscopy Trends in Scaled SOI Technologies"  
"Characterization and TCAD Simulation of 90 nm Technology PMOS Transistor Under Continuous Photoelectric Laser Stimulation for Failure Analysis Improvement"

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## Sommario/riassunto

This volume features the latest research and practical data from the premier event for the microelectronics failure analysis community. The papers cover a wide range of testing and failure analysis topics of practical value to anyone working to detect, understand, and eliminate electronic device and system failures. Case histories and review papers are included, as well as guides to new and unique tools and methodologies, applications and results.

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